

Technical Specifications



Solar Multicrystalline Wafer: 156mm x 156mm

General Characteristics	Features
Product	Multicrystalline silicon wafer
Growth Method	Directional solidification
Conductivity Type	P type
Dopant	Boron
Resistivity	0.5~2Ω.cm
Oxygen Content	8×10^{17} atom/cm ³
Carbon Content	5×10^{16} atom/cm ³
Structural Characteristics	Features
Side	156.0mm ± 0.5mm
Corner diagonal	1.5mm ± 0.5mm
Corner Angle	90°±0.3°
Thickness	200±20μm
Surface	No stain or splash on surface
Mechanical Characteristics	Features
TTV	≤50μm
Bow	≤60μm
Surface	No defect as cut , clean, free from stains, no cracks
Saw Mark	≤15μm